

2CLG15KV/1.0A

1.0A 15kV 80nS--High voltage silicon rectifier stack

HVGT High voltage silicon rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

- 1. High reliability design.
- 2. High voltage design.
- 3. High frequency design..
- 4. Conform to RoHS.
- 5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

- 1. High frequency switching power supply.
- 2. Power supply of laser equipment.
- 3. General purpose high voltage rectifier.
- 4. Other.

MECHANICAL DATA:

- 1. Case: epoxy resin molding.
- 2. Terminal: external lead.
- 3. Net weight: 85 grams (approx).

SHAPE DISPLAY:

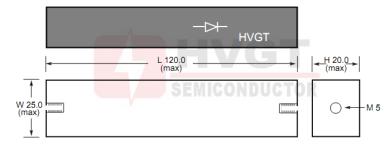


SIZE: (Unit:mm)

HVGT NAME: HVC-122520

HVC-122520 Series

Screw Holes M5



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	Vrrm	Ta=25°C;	15	kV
Average Output Current	IF	Ta=25°C;Resistive Load	1.0	A
Suege Current	Iғsм	Ta=25°C;8.3 mS	30	A
Junction Temperature	TJ		-40~+125	°C
Allowable Operation Case Temperature	Тс		125	°C
Storage Temperature	Тѕтс		-40~+125	°C

ELECTRICAL CHARACTERISTICS: Ta=25°C (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	VF	at 25°C;I _F =I _{F(AV)}	18	V
Maximum Reverse Current	Ir1	at 25°C;V _R =V _{RRM}	5.0	uA
	Ir2	at 100°C;V _R =V _{RRM}	50	uA
Maximum Reverse Recovery Time	Trr	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	80	nS
Junction Capacitance	Сл	at 25°C; V _R =0V; f=1MHz		pF